F10 – Frequency Response

Outline

- Amplifier gain function
- Low frequency coupling/ bypass of a discrete CS amplifier
- High frequency transistor internal capacitive effects
- High frequency MOS and BJT model
- Current gain transition frequency
- Miller's voltage theorem
- Frequency response analysis
 - Gain, dominant pole, short/ open circuit time constants
 - CS amplifier
 - CG amplifier and Cascode amplifier

Reading Guide Sedra/Smith 7ed int

- Chapter 9.1-9.5, (9.6-9.8)
- Appendix F (Bode plot rules)

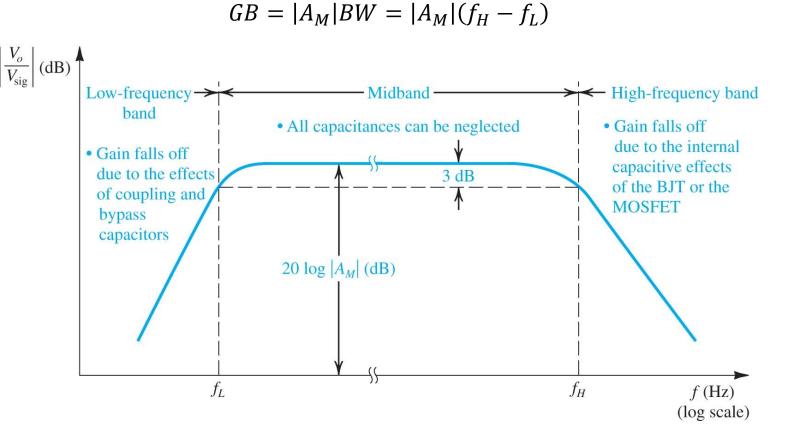
Problems

Sedra/Smith 7ed int

• P9.14, 9.15, 9.24, 9.30, 9.67

Frequency Response of Amplifiers

- Low frequency band, $f < f_L$ (not in dc coupled IC amplifiers)
 - Low corner frequency, f_L
 - Coupling and bypass capacitances
- Midband, $f_L < f < f_H$
 - Bandwidth, $BW = f_H f_L$
 - Midband gain, A_M
 - Neglect capacitances
- High frequency band, $f > f_H$
 - High corner frequency, f_H
 - Intrinsic capacitances



Gain bandwidth product, GB, is a key figure of merit.

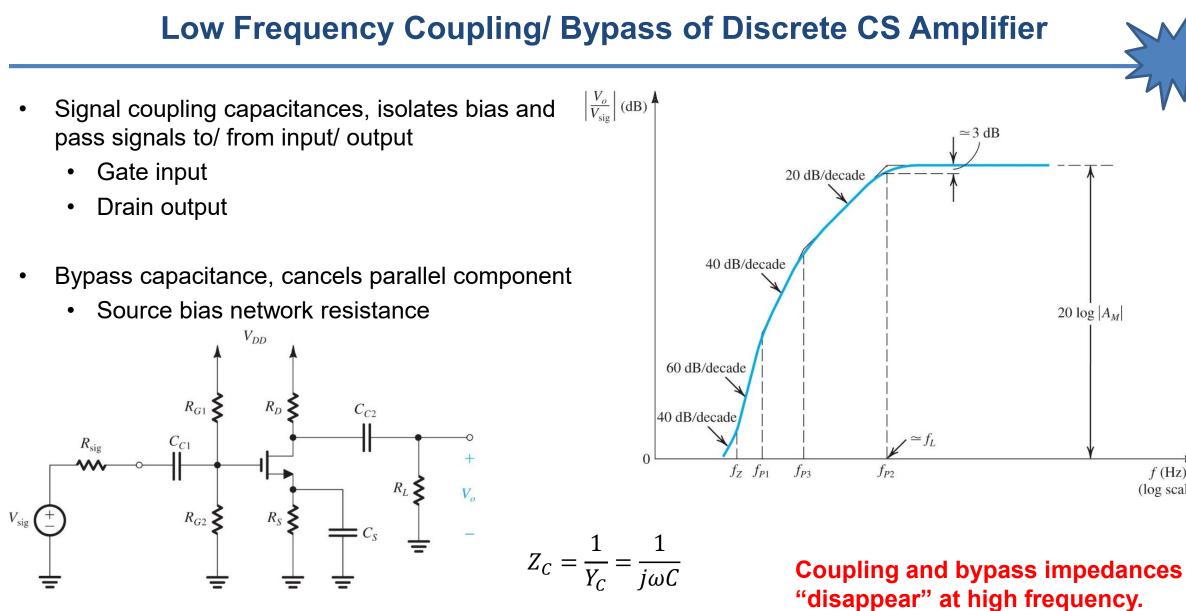
- Amplifier gain function, A(s), where $s = j\omega = j2\pi f$ is the complex angular frequency
 - Low frequency transfer function, $F_L(s)$
 - Midband gain (no frequency dependence), A_M
 - High frequency transfer function, $F_H(s)$

 $A(s) = F_L(s)A_M F_H(s)$

- Transfer functions, F(s), can be found from circuit analysis in the *s*-plane (using immittances)
 - Rational polynomial in s, with m numerator coefficients a_i and $n \ge m$ denominator coefficients b_i
 - Physical (R, G, C, L) networks produce real coefficients, which yield real or conjugate paired roots
 - Numerator roots, $Z_i = -\omega_{Zi}$, a.k.a. transmission zeros (+20 dB/dec and +90° about $|s| \approx \omega_{Zi}$)
 - Denominator roots, $P_j = -\omega_{Pj}$, a.k.a. poles, natural modes (-20 dB/dec and -90° about $|s| \approx \omega_{Pj}$)

$$F(s) = \frac{\sum_{i=0}^{m} a_i s^i}{\sum_{j=0}^{n} b_j s^j} = a_m \frac{\prod_{i=1}^{m} (s - Z_i)}{\prod_{j=1}^{n} (s - P_j)} = A \frac{\prod_{i=1}^{m} \left(1 + \frac{s}{\omega_{Z_i}}\right)}{\prod_{j=1}^{n} \left(1 + \frac{s}{\omega_{P_j}}\right)}$$

Poles may come with up to an equal number of zeros.



f(Hz)(log scale)

MOSFET Internal Capacitive Effects

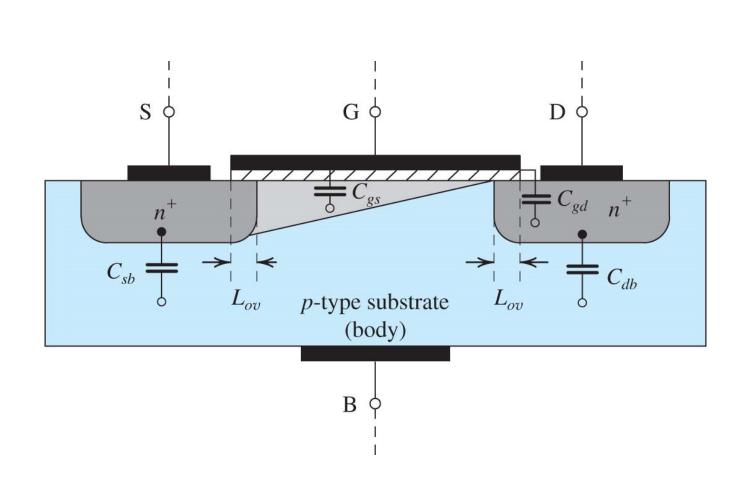
- Channel capacitance
 - Gate-source

$$C_{ch} = \frac{2}{3} WLC_{ox}$$

- Overlap capacitances
 - Gate-source
 - Drain-source

 $C_{ov} = W L_{ov} C_{ox}$

- Junction capacitances
 - Source-body
 - Drain-body



High Frequency MOSFET Model (recap)

Transconductance

$$g_m = k'_n \left(\frac{W}{L}\right) V_{OV} = \sqrt{2k'_n \left(\frac{W}{L}\right) I_D} = \frac{2I_D}{V_{OV}}$$

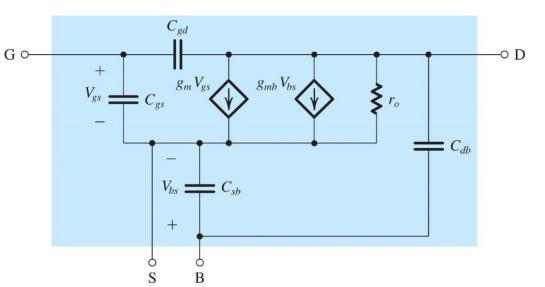
• Output resistance

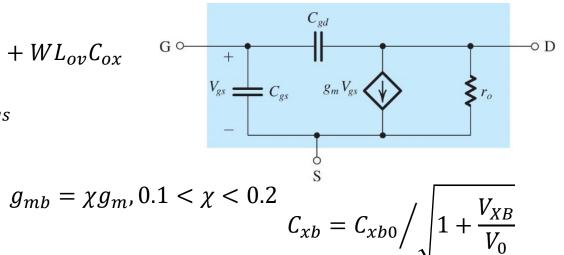
$$r_o = \frac{1}{\lambda I'_D} = \frac{L}{\lambda' I'_D} = \frac{LV'_A}{\lambda' I'_D} = \frac{V_A}{I'_D}$$

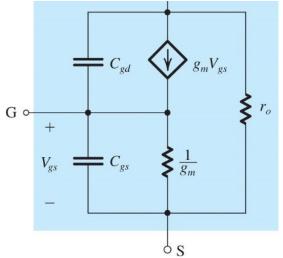
• Channel and overlap capacitance

$$C_{gs} = C_{ch} + C_{ov} = \frac{2}{3}WLC_{ox} + WL_{ov}C_{ox}$$
$$C_{ds} = C_{ov} = WL_{ov}C_{ox} < C_{gs}$$

- (Body)
 - Transconductance $g_{mb} =$
 - Junction capacitance







High Frequency BJT Model (recap)

Transconductance -OC $g_m = \frac{I_C}{V_T}$ $\int g_m V_\pi$ Output resistance • $r_o = \frac{V_A}{I'_a}$ Metal contact p p n Base/ emitter resistance • Eo--0 C Emitter Collector Base QC $r_{\pi} = \frac{\beta}{a_m} \qquad r_e = \frac{r_{\pi}}{(1+\beta)}$ region region region Base access resistance • $\langle \mathbf{v} \rangle g_m V_{\pi}$ r_x Bo-- r_{x} $V_{\pi} = C_{\pi}$ Base transit and junction capacitances ٠ $C_{\pi} = C_{de} + C_{je} \approx \tau_F g_m + 2C_{je0}$ $C_{\mu} = C_{jc} = C_{jc0} / \left(1 + \frac{V_{CB}}{V_{0c}}\right)^m$, 0.3 < m < 0.5ÓΕ

CS(/ CE) Amplifier Cutoff Frequency

- The frequency where the transistor current gain transitions from above unity to below unity, i.e. where the gain cuts off
 - Current gain transition frequency, f_T

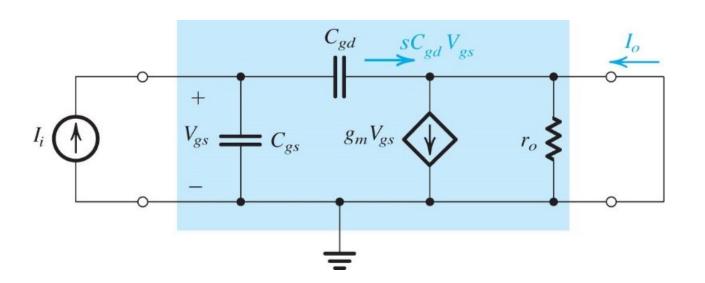
MOSFET

$$f_T \approx \frac{g_m}{2\pi (C_{gs} + C_{gd})}$$

 $A_i(f_T) = \frac{I_o}{I_i} = 1$

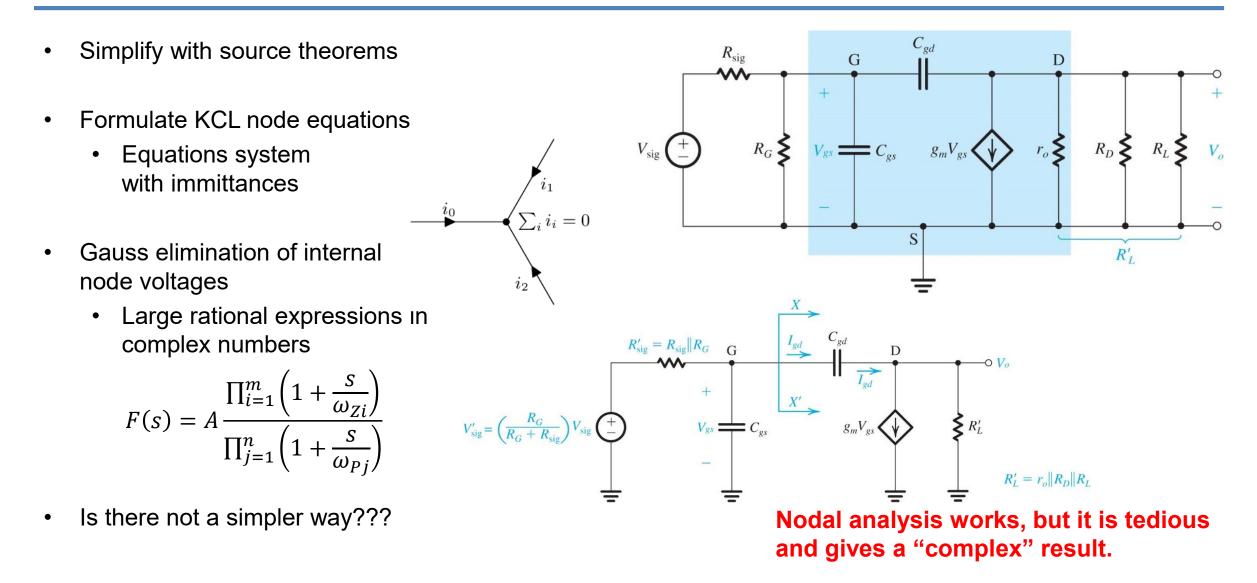
$$f_T \approx \frac{g_m}{2\pi (C_\pi + C_\mu)}$$





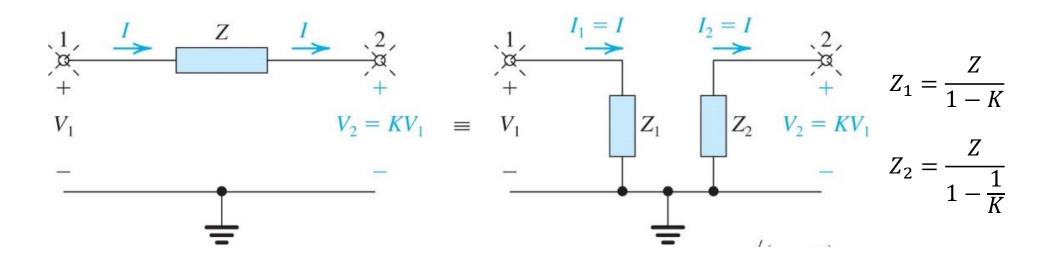


Gain Function by Nodal Analysis: CS Amplifier



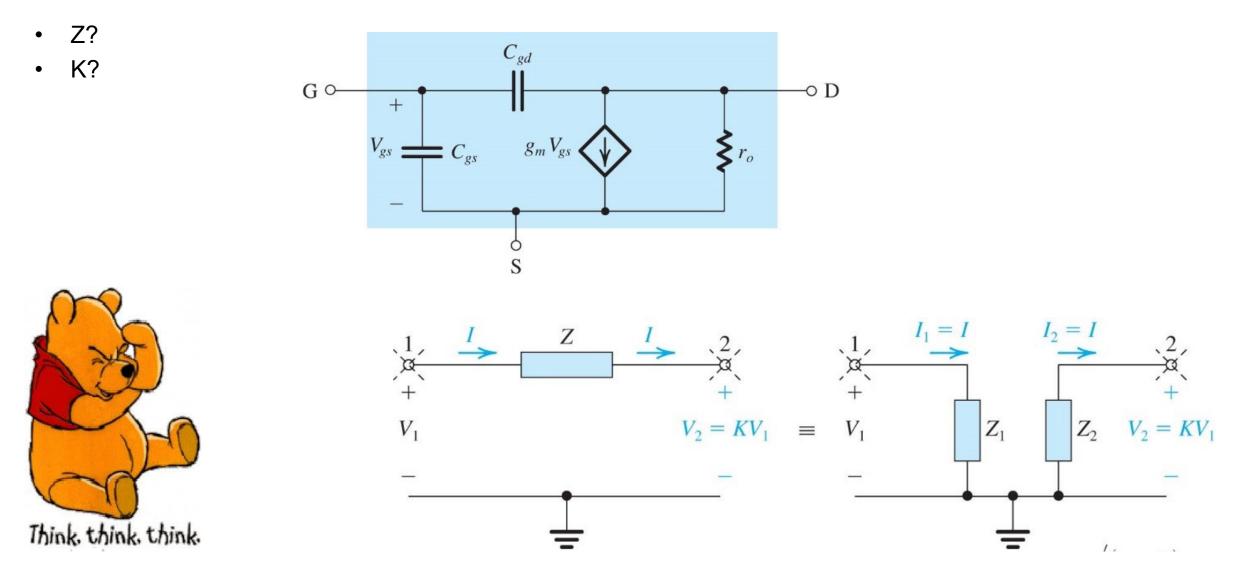
BREAK

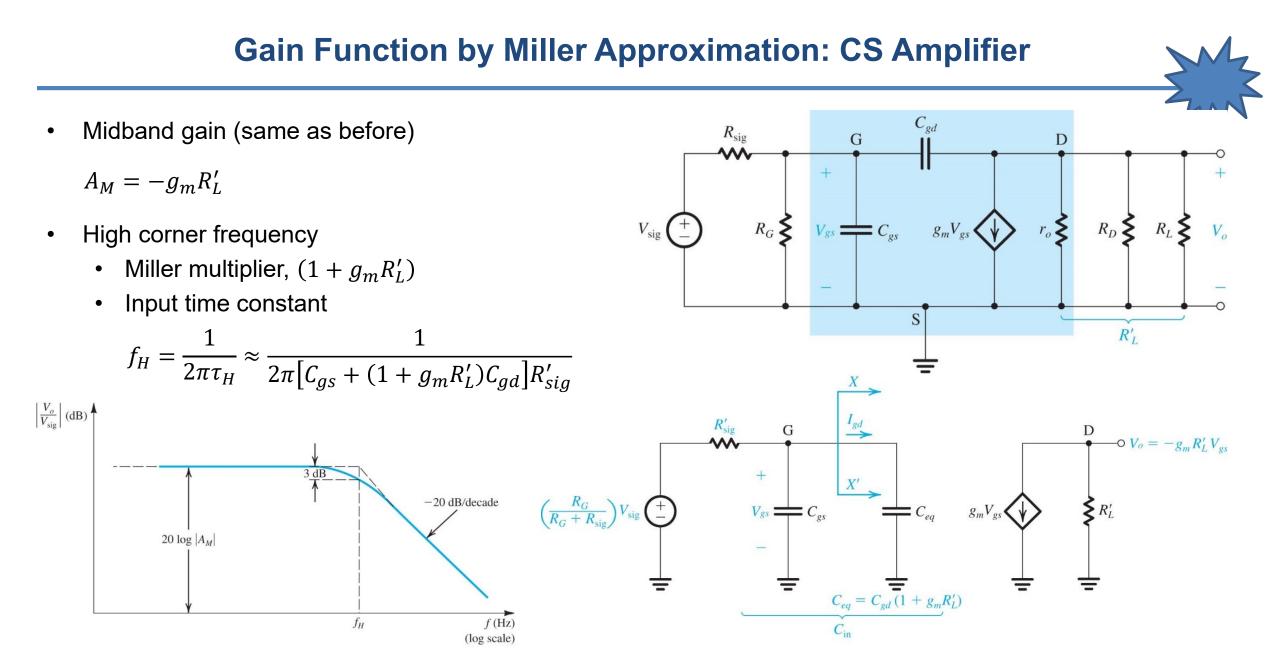
- Impedance, *Z*, connected between dependent nodes 1 and 2, where voltages are $V_2 = KV_1$ related to a common node
- Equivalent to impedances, Z_1 and Z_2 , to common terminal



Only valid for finding input impedance, since external circuit must remain invariant.

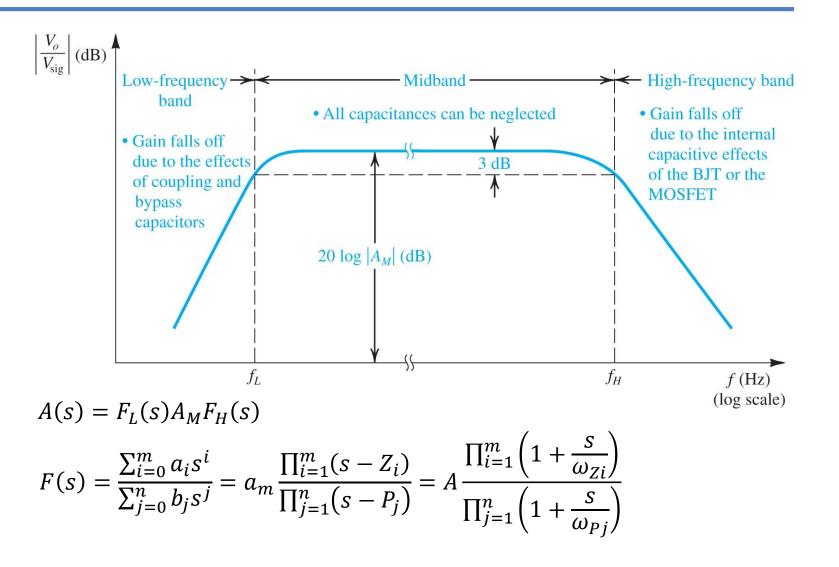
How can Miller's theorem be adapted to transistor analysis?



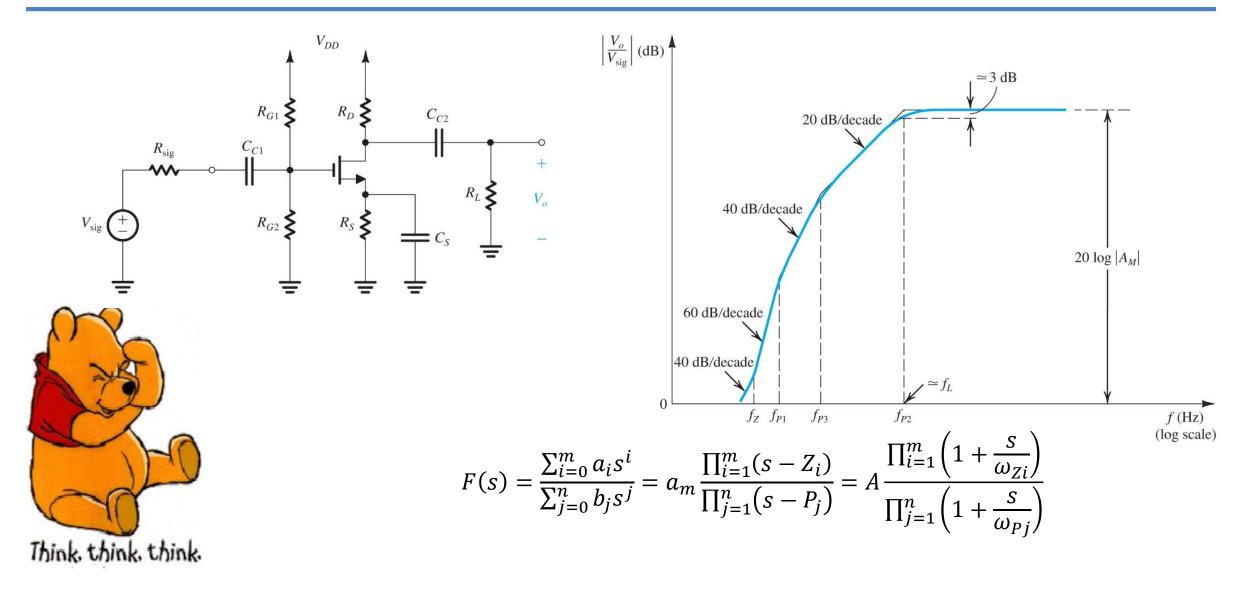


Frequency Response – Gain Function Zeros and Poles

- Low frequency band, $f < f_L$ (not in dc coupled IC amplifiers)
 - Low corner frequency, f_L
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- Midband, $f_L < f < f_H$
 - Bandwidth, $BW = f_H f_L$
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 - High corner frequency, f_H
 - Intrinsic capacitances



Of all the zero and pole frequencies, which is important?



Dominant Poles

- Estimate low and high corner frequencies of midband from highest and lowest respective pole frequency
- Low corner dominant pole, P_L
 - Defines the "turn" towards midband
 - Pole related to coupling and bypass capacitors, disconnects the input/output at low frequency
 - Higher frequency than all else by some margin...
- High corner dominant pole, P_H
 - Defines the "turn" towards cutoff
 - A pole related to intrinsic input and output capacitors, short circuits the input/output at high frequency
 - Lower frequency than all else by some margin...

$$F_L(s) \approx \frac{\frac{S}{\omega_L}}{1 + \frac{S}{\omega_L}} \text{ where } Z_L = 0 \text{ and } P_L = -\omega_L$$
$$\omega_L = \frac{1}{\tau_L} \approx \sqrt{\sum_{j=1}^n \omega_{Pj} - 2\sum_{i=1}^m \omega_{Zi}} \approx \omega_{P,max}$$

$$F_{H}(s) \approx \frac{1}{1 + \frac{s}{\omega_{H}}} \text{ where } P_{H} = -\omega_{H}$$
$$\omega_{H} = \frac{1}{\tau_{H}} \approx \frac{1}{\sqrt{\sqrt{\sum_{j=1}^{n} \frac{1}{\omega_{Pj}} - 2\sum_{i=1}^{m} \frac{1}{\omega_{Zi}}}} \approx \omega_{P,min}$$

Two octaves (x4) of separation is the rule of thumb for the dominant approximation.

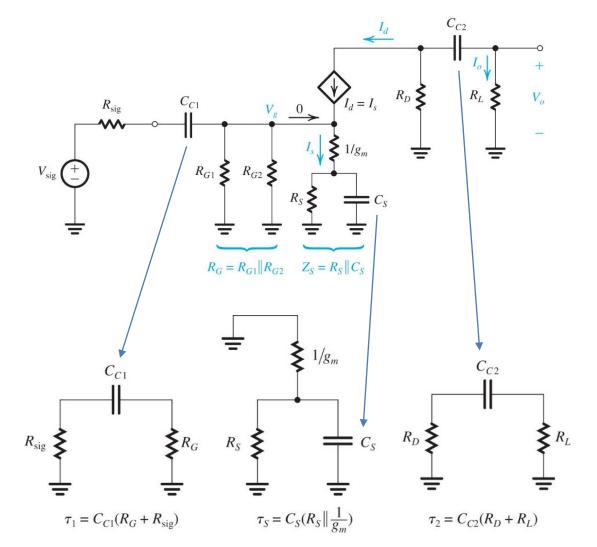
Low Corner: Method of Short Circuit Time Constants (SCTCs)

 Assume that one capacitor generates a dominant pole in the low frequency transfer function

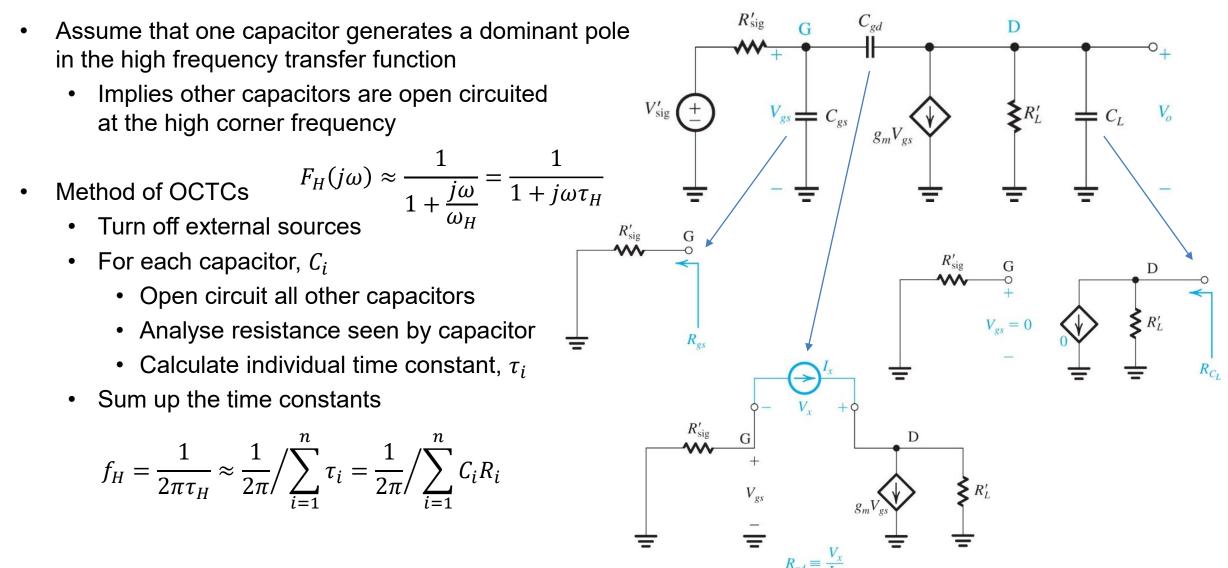
 $F_L(j\omega) \approx \frac{1}{2}$

- Implies other capacitors are short circuited at the low corner frequency
- Method of SCTCs
 - Turn off external sources
 - For each capacitor, C_i
 - · Short circuit all other capacitors
 - · Analyse resistance seen by capacitor
 - Calculate individual time constant, τ_i
 - Sum up the inverse time constants

$$f_L = \frac{1}{2\pi\tau_L} \approx \frac{1}{2\pi} \sum_i \frac{1}{\tau_i} = \frac{1}{2\pi} \sum_i \frac{1}{C_i R_i}$$



High Corner: Method of Open Circuit Time Constants (OCTCs)



OCTC: CS Amplifier

 $V_{\rm sig}$

R_{sig}

 R_G

 $V_{gs} = C_{gs}$

- Method of OCTCs
 - Turn off external sources
 - For each capacitor, C_i
 - Open circuit all other capacitors
 - Analyse resistance seen by capacitor
 - Calculate individual time constant, τ_i
 - Sum up the time constants

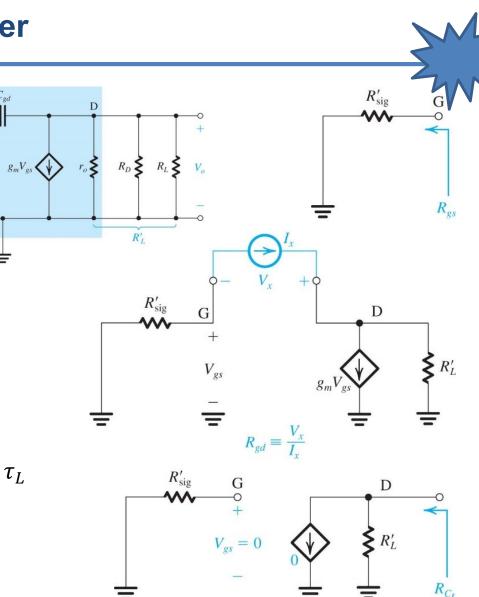
$$\tau_{gs} = C_{gs}R_{gs} = C_{gs}R'_{sig}$$

$$\tau_{gd} = C_{gd}R_{gd} = C_{gd}([1 + g_m R'_L]R'_{sig} + R'_L)$$

$$\tau_L = C_L R_{CL} = C_L R'_L$$

$$\tau_H \approx \tau_{gs} + \tau_{gd} + \tau_L$$
$$f_H = \frac{1}{2\pi\tau_H}$$

- If signal source resistance high
 - Miller effect dominates corner frequency

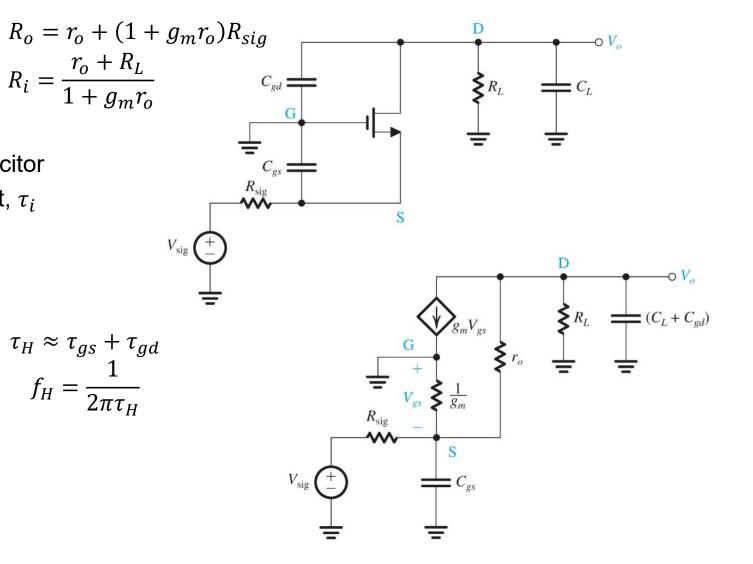


OCTC: CG Amplifier

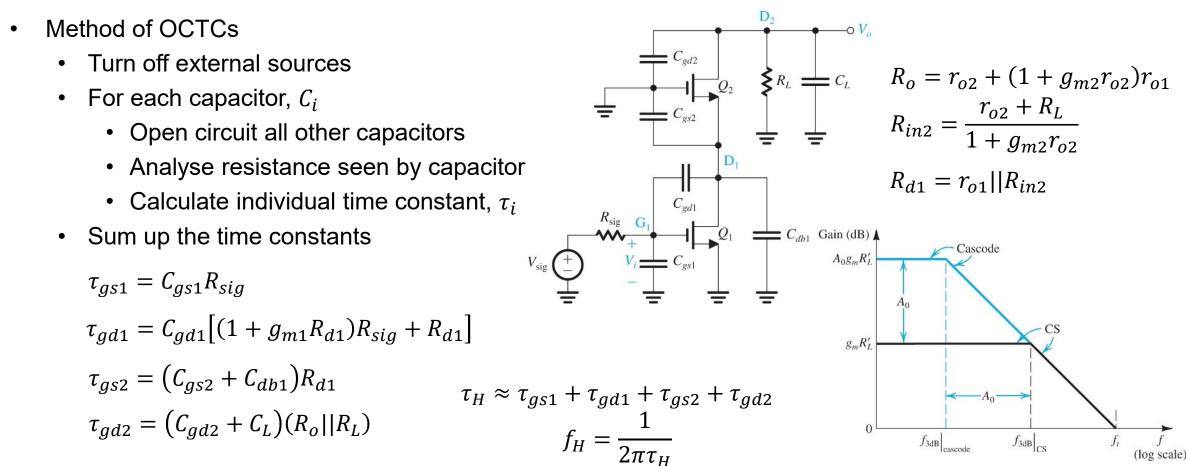
- Method of OCTCs
 - Turn off external sources
 - For each capacitor, C_i
 - Open circuit all other capacitors
 - Analyse resistance seen by capacitor
 - Calculate individual time constant, τ_i
 - Sum up the time constants

 $\tau_{gs} = C_{gs} (R_{sig} || R_i)$ $\tau_{gd} = (C_{gd} + C_L) (R_L || R_o)$

- Capacitances to grounded gate
 - Effectively "moved" to ground
 - Analysis simplified



OCTC: Cascode Amplifier



- If signal source resistance negligible
 - Increased dc gain, reduced BW, same cutoff w.r.t. CS

Cascode input, middle node (D1,S2), or output may dominate...

(Differential Amplifier: Common Mode Gain and CMRR)

